Product data sheet

1. General description

Hyperfast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

2. Features and benefits

- Extremely fast switching
- Low thermal resistance
- · Low reverse recovery current
- Isolated package
- · Reduces switching loss in associated MOSFET

3. Applications

- Half-bridge or full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			600			V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; $T_h \le 25$ °C; Fig. 1; Fig. 2		15			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 25 °C; square-wave pulse	30			А	
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200				А
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220			А	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 4</u>		-	1.89	2.9	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.32	2.03	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.64	2.34	V
Dynamic	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 5		-	35	55	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	
2	А	anode		К —— А
mb	n.c.	mounting base; isolated		001aaa020
			1 2	
			SOD113 (2-lead TO-220F)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC15X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC15X-600	BYC15X-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	δ = 1.0 ; square-wave pulse; $T_h \le 100 ^{\circ}\text{C}$;	500	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 25$ °C; Fig. 1; Fig. 2	15	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 25 °C$; square-wave pulse	30	А
I _{FSM}	non-repetitive peak	$t_p = 10 \text{ ms; } T_{j(init)} = 25 \text{ °C; sine-wave pulse}$	200	А
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

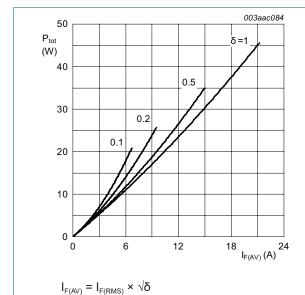
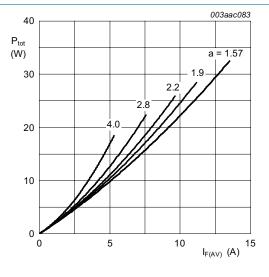


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

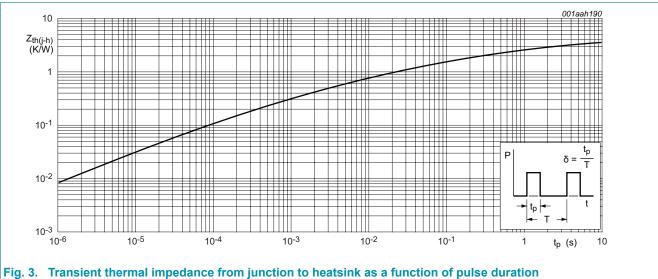
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 3	-	-	3.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

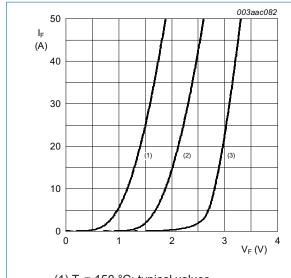
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	PF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.89	2.9	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.32	2.03	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.64	2.34	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	12	200	μA
		V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } Fig. 5$	-	35	55	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		19	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 5$	-	32	40	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 5$	-	9.5	12	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 5$	-	3	7.5	А
V_{FR}	forward recovery voltage	I _F = 15 A; dI _F /dt = 100 A/μs; T _i = 25 °C; <u>Fig. 6</u>	-	8	11	V



(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 4. Forward current as a function of forward voltage

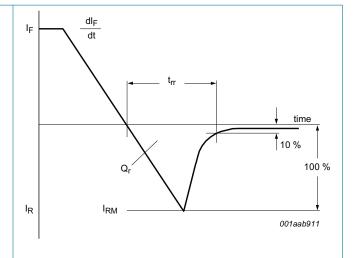
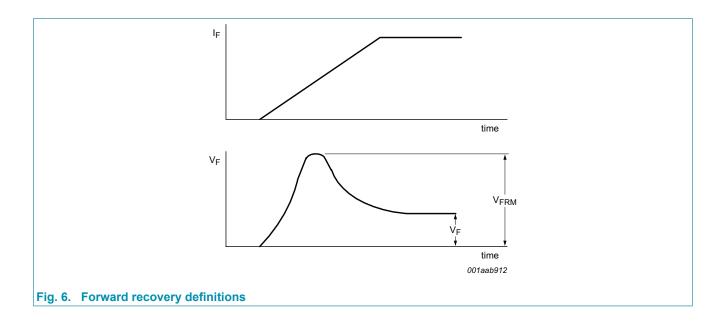


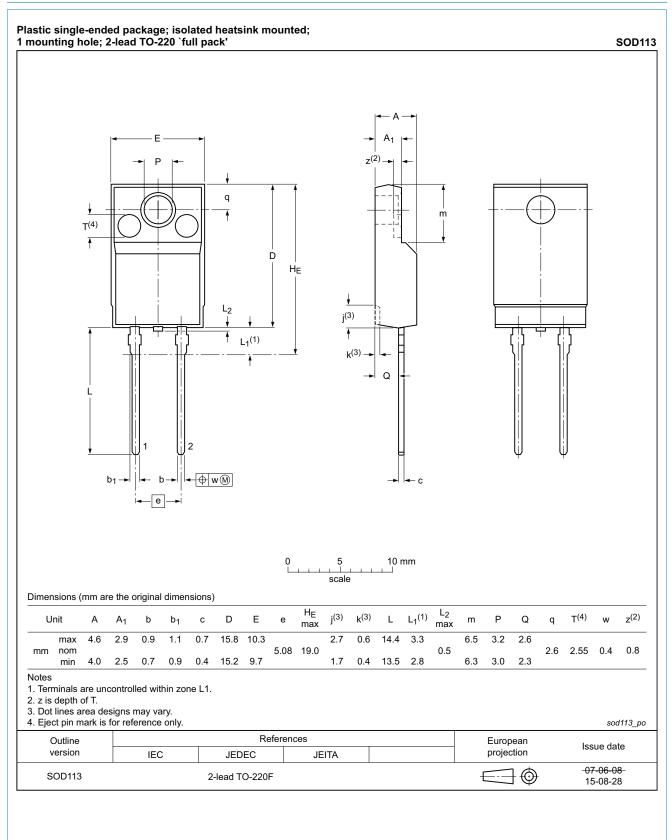
Fig. 5. Reverse recovery definitions

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12. Package outline



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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